

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-45 (Canceled)

46. (Currently Amended) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip:

a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing the main surface of the semiconductor chip, a second surface opposite to the first surface and a through hole provided thereof;

a plurality of conductive patterns formed on the first surface of the base resin film, the conductive patterns extending near the through hole; and

an insulating film formed on the first surface of the base resin film and the conductive patterns, the ~~insulating film~~ base resin having a plurality of electrode holes for exposing a part of the conductive patterns

~~a plurality of inner leads connecting the electrodes with the conductive patterns through the through holes,~~ wherein the conductive patterns extending in the through hole are connected with the electrodes.

47. (Previously presented) A semiconductor device according to claim 46, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

48. (Previously presented) A semiconductor device according to claim 46, further comprising a plurality of solder balls formed on the electrode holes.

49. (Previously presented) A semiconductor device according to claim 46, wherein the base resin film is formed on the main surface, back surface and side surfaces of the semiconductor chip.

50. (Previously presented) A semiconductor device according to claim 46, wherein the base resin film is covered by elastic resin.

51. (Previously presented) A semiconductor device according to claim 50, wherein the elastic resin is polyimide.

52. (Currently Amended) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip;

a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing said semiconductor chip, a second surface opposite to the first surface and a through hole provided thereof;

a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns extending near the through hole;
an insulating film formed on the second surface of the base resin film and conductive patterns, the ~~insulating film~~ base resin having a plurality of electrode holes for exposing a part of the conductive patterns; ~~and~~
~~a plurality of inner leads connecting the electrodes with the conductive patterns through the through holes, wherein the conductive patterns extending in the through hole are connected with the electrodes.~~

53. (Previously presented) A semiconductor device according to claim 52, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

54. (Previously presented) A semiconductor device according to claim 52, further comprising a plurality of solder balls formed on the electrodes holes.

55. (Previously presented) A semiconductor device according to claim 52, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.

56. (Previously presented) A semiconductor device according to claim 52, wherein the base resin film is covered by elastic resin.

57. (Previously presented) A semiconductor device according to claim 56, wherein the elastic resin is polyimide.

58. (Currently Amended) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip;

a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing said semiconductor chip and a second surface opposite the first surface;

a plurality of electrode patterns formed on the first surface of the base resin film;

a first insulating film formed on the first surface of the base resin film, the first insulating film having a plurality of first electrode holes for exposing the electrode patterns;

a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns electrically connected to the electrode patterns; and

a second insulating film formed on the second surface of the base resin film and the conductive patterns, ~~the insulating film~~ base resin having a plurality of second electrode holes for exposing a part of the conductive patterns.

59. (Previously presented) A semiconductor device according to claim 58, wherein the main surface and the side surface of the semiconductor chip are covered by molding resin.

60. (Previously presented) A semiconductor device according to claim 58, further comprising a plurality of solder balls formed on the second electrodes holes.
61. (Previously presented) A semiconductor device according to claim 58, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.
62. (Previously presented) A semiconductor device according to claim 61, wherein the base resin film is substantially surrounding the semiconductor chip.
63. (Previously presented) A semiconductor device according to claim 58, wherein the base resin is covered by elastic resin.
64. (Previously presented) A semiconductor device according to claim 63, wherein the elastic resin is polyimide.